

Supporting Information

Photovoltage Junction Memtransistor for Optoelectronic In-memory Computing

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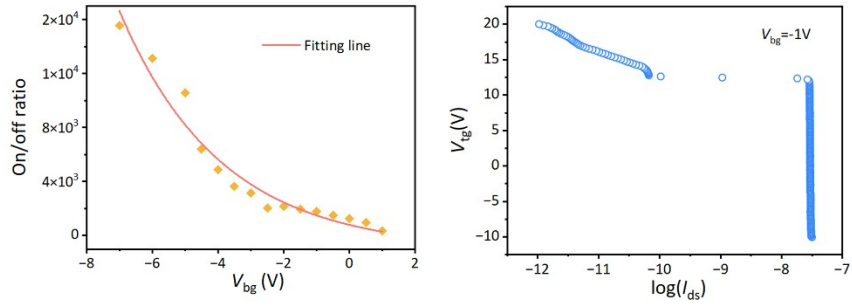


Figure S1. Electrical on/off ratio change with V_{bg} and subthreshold swing (SS) calculation by differential coefficient V_{tg} - $\log(I_{ds})$ curve.

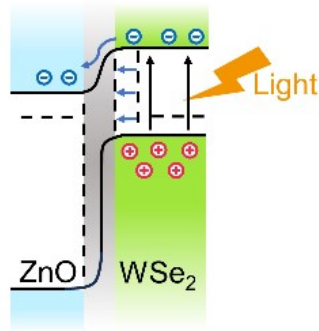


Figure S2. Photo-excited electrons and holes transfer in band under light.

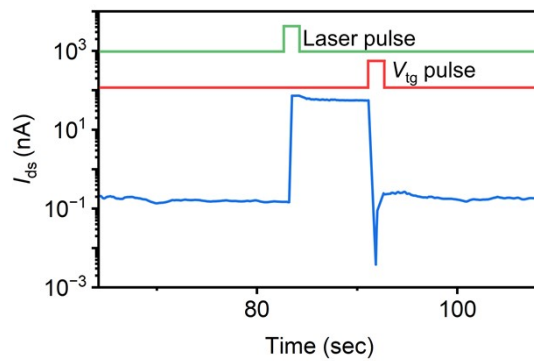


Figure S3. The off-current value reverts to the original value after electric erasing.

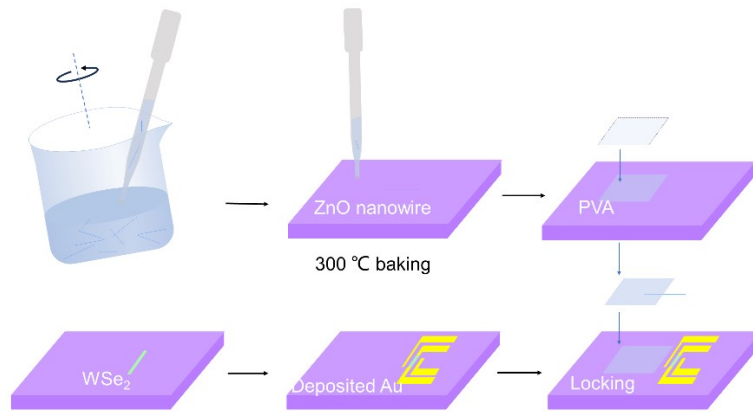


Figure S4. the schematic illustration of transfer method of optical memory device based ZnO/WSe₂ Junction Field-effect Transistor.